

NTB5605P, NTB5605

MOSFET – Power, P-Channel, D²PAK

-60 V, -18.5 A

Features

- Designed for Low $R_{DS(on)}$
- Withstands High Energy in Avalanche and Commutation Modes
- AEC Q101 Qualified – NTB5605
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Supplies
- PWM Motor Control
- Converters
- Power Management

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	−60	V
Gate-to-Source Voltage			V _{GS}	± 20	V
Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	−18.5	A
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	88	W
Pulsed Drain Current	t _p = 10 μs		I _{DM}	−55	A
Operating Junction and Storage Temperature			T _J , T _{STG}	−55 to 175	°C
Single Pulse Drain-to-Source Avalanche Energy (V _{DD} = 25 V, V _{GS} = 5.0 V, I _{PK} = 15 A, L = 3.0 mH, R _G = 25 Ω)			E _{AS}	338	mJ
Lead Temperature for Soldering Purposes (1/8 in from case for 10 s)			T _L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) – Steady State	$R_{\theta JC}$	1.7	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. When surface mounted to an FR4 board using 1" pad size (Cu Area 1.127 in²).
2. When surface mounted to an FR4 board using the minimum recommended pad size (Cu Area 0.41 in²).

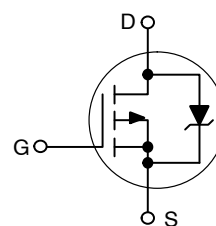


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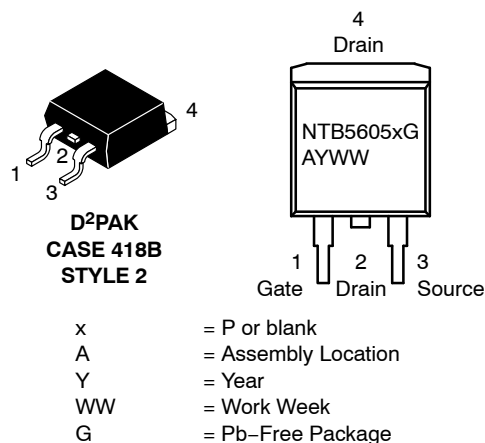
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
-60 V	120 m Ω @ -5.0 V	-18.5 A

P-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NTB5605PT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NTBV5605T4G	D ² PAK (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(Br)DSS}	V _{GS} = 0 V, I _D = -250 μA	-60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(Br)DSS} /T _J			-64		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, T _J = 25°C			-1.0	μA
		V _{DS} = -60 V, T _J = 125°C			-10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = -250 μA	-1.0	-1.5	-2.0	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -5.0 V, I _D = -8.5 A V _{GS} = -5.0 V, I _D = -17 A		120 140	140	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -10 V, I _D = -8.5 A		12		S
Drain-to-Source On Voltage	V _{DS(on)}	V _{GS} = -5.0 V, I _D = -8.5 A			-1.3	V

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = -25 V		730	1190	pF
Output Capacitance	C _{oss}			211	300	
Reverse Transfer Capacitance	C _{rss}			67	120	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -5.0 V, V _{DS} = -48 V, I _D = -17 A		13	22	nC
Gate-to-Source Charge	Q _{GS}			4.0		
Gate-to-Drain Charge	Q _{GD}			7.0		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(on)}	V _{GS} = -5.0 V, V _{DD} = -30 V, I _D = -17 A, R _G = 9.1 Ω		12.5	25	ns
Rise Time	t _r			122	183	
Turn-Off Delay Time	t _{d(off)}			29	58	
Fall Time	t _f			75	150	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -17 A	T _J = 25°C T _J = 125°C	-1.55 -1.4	-2.5	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = -17 A		60		ns
Charge Time	t _a			39		
Discharge Time	t _b			21		
Reverse Recovery Charge	Q _{RR}			0.14		nC

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

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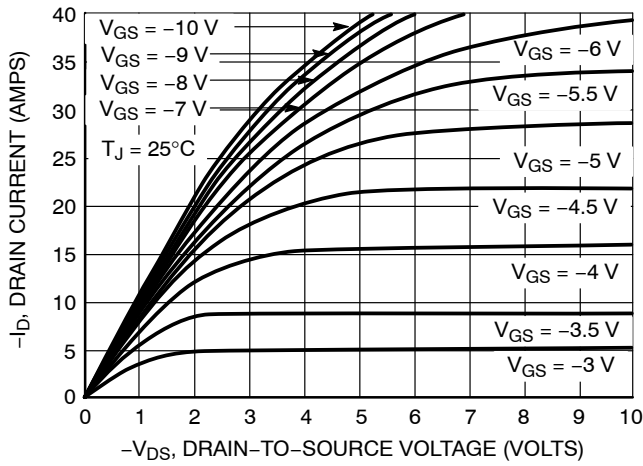


Figure 1. On-Region Characteristics

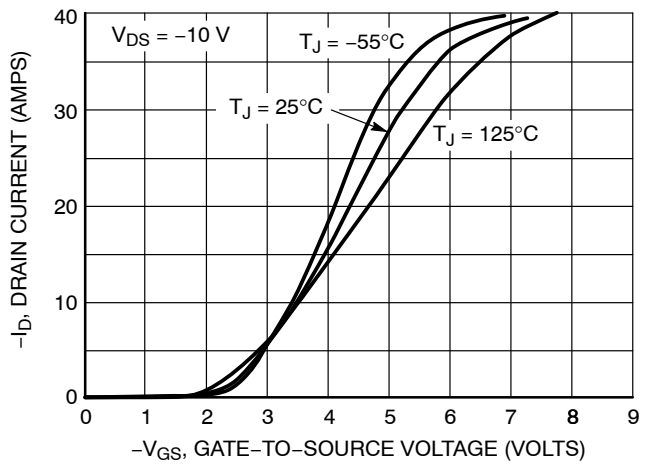


Figure 2. Transfer Characteristics

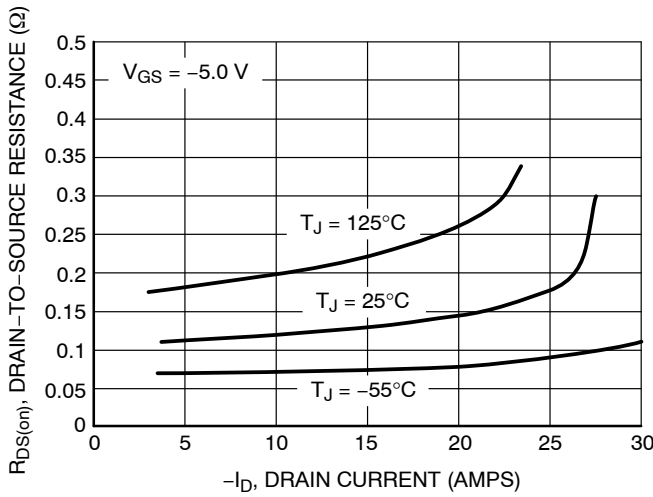


Figure 3. On-Resistance vs. Drain Current and Temperature

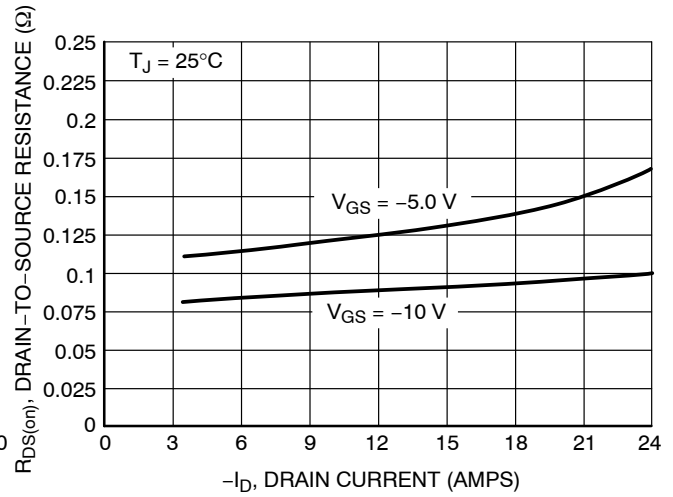


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

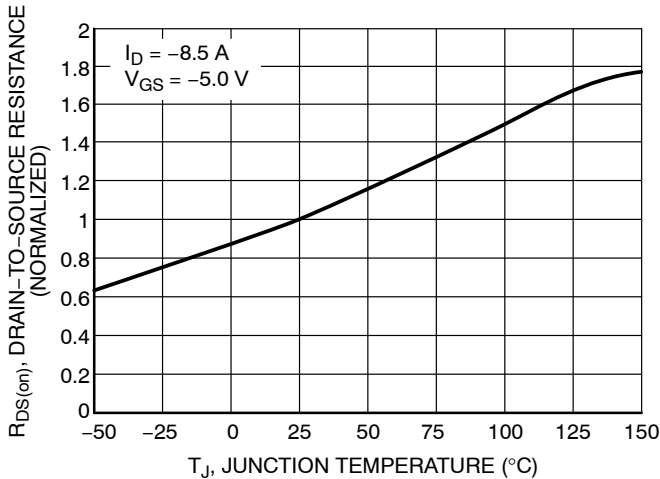


Figure 5. On-Resistance Variation with Temperature

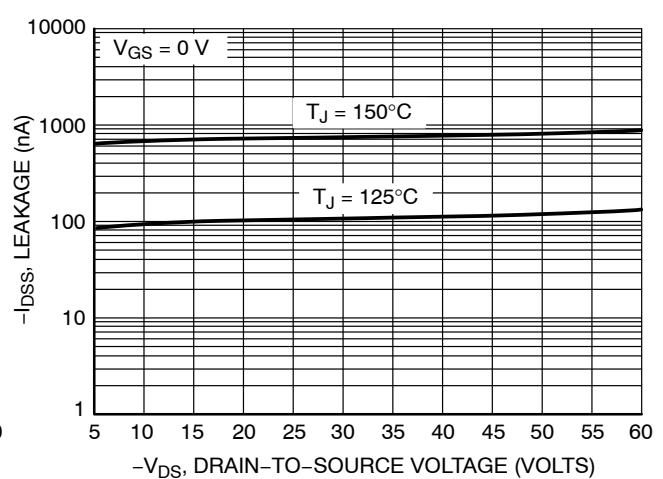


Figure 6. Drain-to-Source Leakage Current vs. Voltage

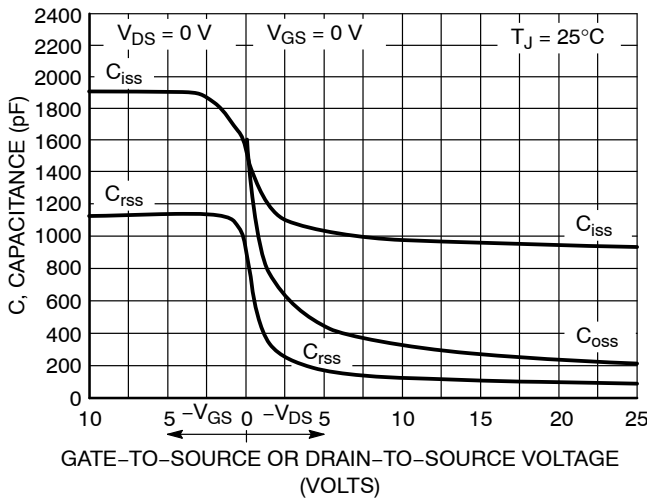


Figure 7. Capacitance Variation

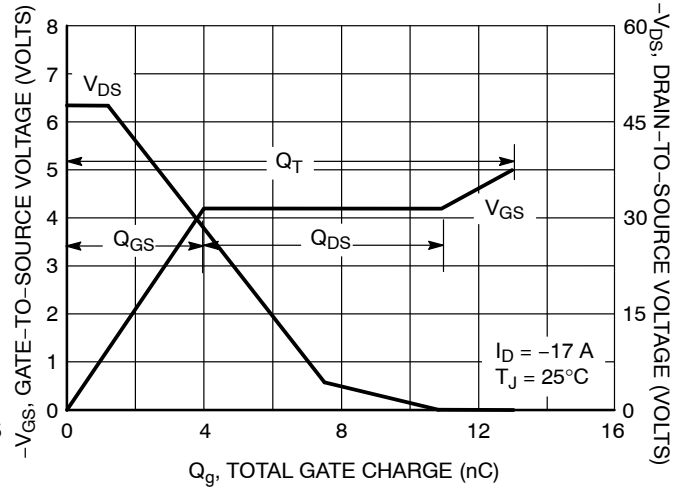


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

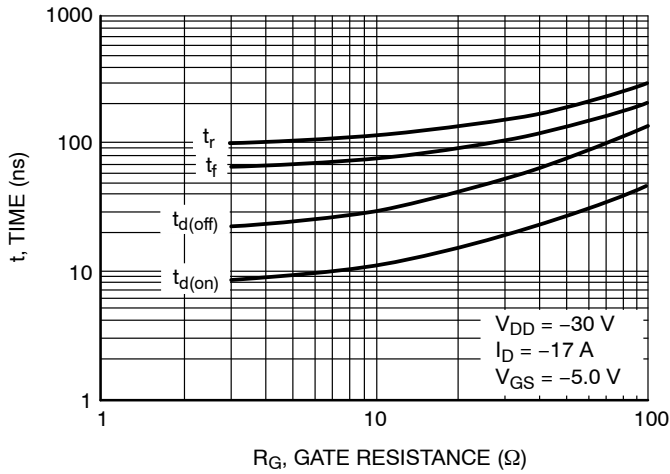


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

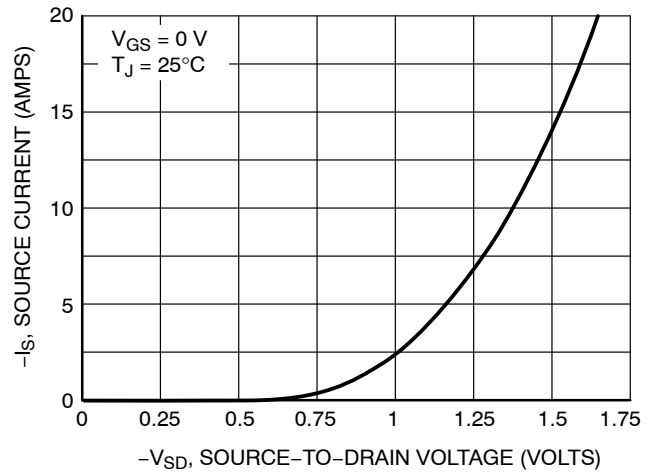


Figure 10. Diode Forward Voltage vs. Current

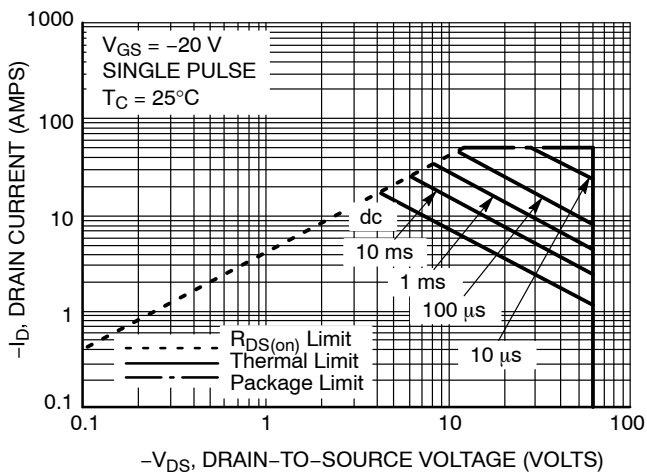


Figure 11. Maximum Rated Forward Biased Safe Operating Area

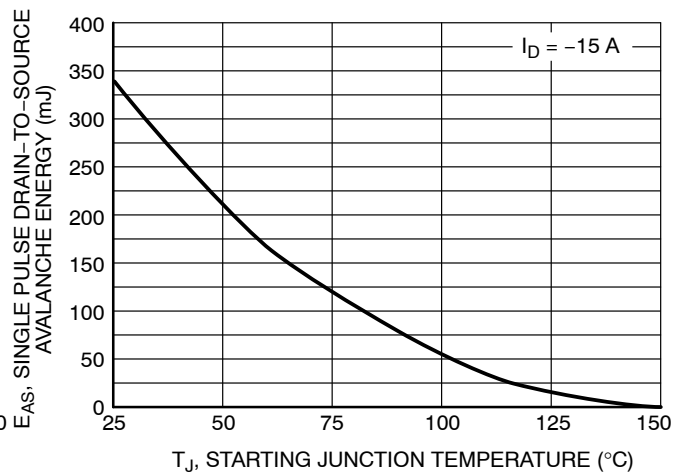


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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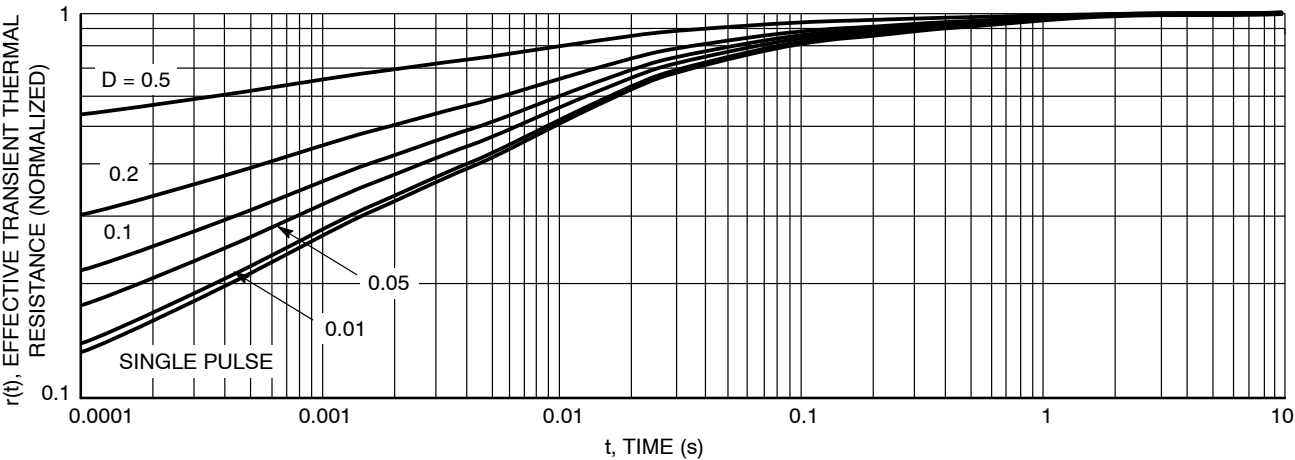


Figure 13. Thermal Response

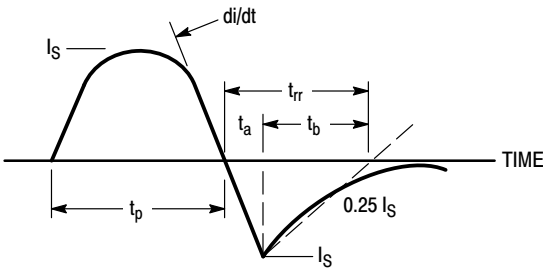


Figure 14. Diode Reverse Recovery Waveform



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CASE 418B-04
ISSUE L

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SCALE 1:1

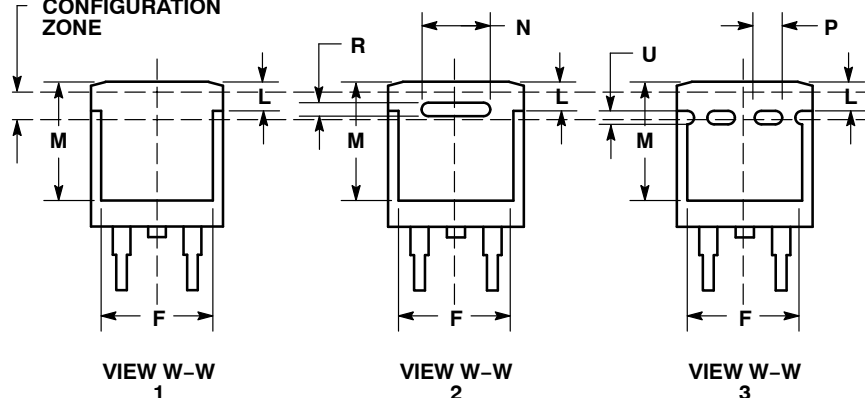


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

VARIABLE
CONFIGURATION
ZONE



STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

- PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

- PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:

- PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:

- PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

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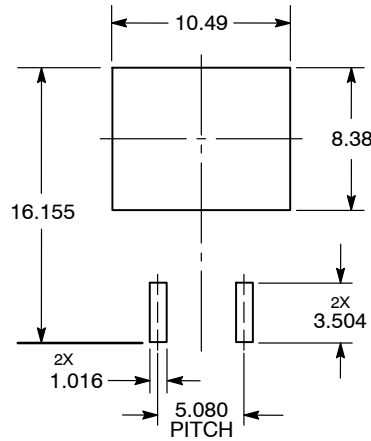
**GENERIC
MARKING DIAGRAM***



xx = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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